

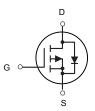
Description

The HXY5P04I uses advanced trench technology to provide excellent $R_{DS(ON)}$, low gate charge and operation with gate voltages as low as 4.5V. This device is suitable for use as a Battery protection or in other Switching application.



General Features

 V_{DS} =-40V I_{D} =-5A $R_{DS(ON)} < 55 m \Omega$ @ V_{GS} =-10V $R_{DS(ON)} < 88 m \Omega$ @ V_{GS} =-4.5V



Application

Battery protection

Load switch

Uninterruptible power supply

P-Channel MOSFET

Package Marking and Ordering Information

Product ID	Pack	Marking	Qty(PCS)
HXY5P04I	SOT-23		3000

Absolute Maximum Ratings (T_A=25 ℃ unless otherwise noted)

Symbol	Parameter	Limit	Unit
V _{DS}	Drain-Source Voltage	-40	V
V _{GS}	Gate-Source Voltage	±20	V
I _D	Drain Current-Continuous	-5	А
Ірм	Drain Current-Pulsed (Note 1)	-22	А
P _D	Maximum Power Dissipation	2	W
Тл,Твтв	Operating Junction and Storage Temperature Range	-55 To 150	°C
Reja	Thermal Resistance,Junction-to-Ambient (Note 2)	65	°C/W



Electrical Characteristics (T_J=25°C unless otherwise specified)

Symbol	Parameter	Test Condition	Min.	Тур.	Max.	Units
Off Charac	cteristic		•		1	ı
V _{(BR)DSS}	Drain-Source Breakdown Voltage	V _{GS} =0V, I _D = -250μA	-40	-	-	V
I _{DSS}	Zero Gate Voltage Drain Current	V _{DS} = -40V, V _{GS} =0V	-	-	-1	μA
I _{GSS}	Gate to Body Leakage Current	V _{DS} =0V, V _{GS} = ±20V	-	_	±100	nA
On Charac	cteristics					
V _{GS(th)}	Gate Threshold Voltage	V _{DS} =V _{GS} , I _D = -250μA	-1.0	-1.6	-2.5	V
,	Static Drain-Source on-Resistance	V _{GS} = -10V, I _D = -5A	-	47	55	mΩ
$R_{DS(on)}$		V _{GS} = -4.5V, I _D = -4A	-	62	88	
Dynamic (Characteristics				•	•
C _{iss}	Input Capacitance	V _{DS} = -20V, V _{GS} =0V, f=1.0MHz	-	869	-	pF
C _{oss}	Output Capacitance		-	94	-	pF
C _{rss}	Reverse Transfer Capacitance		-	69	-	pF
Qg	Total Gate Charge	V _{DS} = -20V, I _D = -4A,	-	17.3	-	nC
Q _{gs}	Gate-Source Charge		-	3.2	-	nC
Q_gd	Gate-Drain("Miller") Charge	V _{GS} = -10V	-	4.3	-	nC
Switching	Characteristics					
t _{d(on)}	Turn-on Delay Time		-	10.3	-	ns
t _r	Turn-on Rise Time	V_{DS} = -20V, I_{D} = -4A,	-	4.3	-	ns
t _{d(off)}	Turn-off Delay Time	V_{GS} = -10V, R_{GEN} =3 Ω	-	39	-	ns
t _f	Turn-off Fall Time		-	46.5	-	ns
Drain-Sou	rce Diode Characteristics and Maxi	mum Ratings				
Is	Maximum Continuous Drain to Source Diode Forward Current		-	-	- 5	Α
I _{SM}	Maximum Pulsed Drain to Source D	iode Forward Current	-	-	-22	Α
V _{SD}	Drain to Source Diode Forward Voltage	V _{GS} =0V, I _S = -5.5A	-	-0.8	-1.2	V
trr	Reverse Recovery Time	V _{GS} =0V, I _S = -5.5A,	-	17	-	ns
Qrr	Reverse Recovery Charge	di/dt=100A/µs	-	11.5	-	nC

Notes:1. Repetitive Rating: Pulse Width Limited by Maximum Junction Temperature

^{2.} Pulse Test: Pulse Width≤300µs, Duty Cycle≤2%



Typical Performance Characteristics

Figure1: Output Characteristics

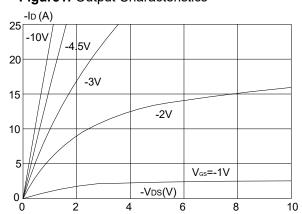


Figure 3:On-resistance vs. Drain Current

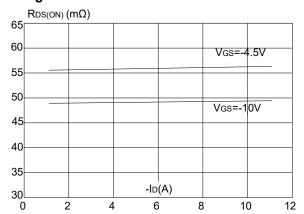


Figure 5: Gate Charge Characteristics

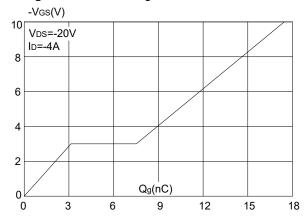


Figure 2: Typical Transfer Characteristics

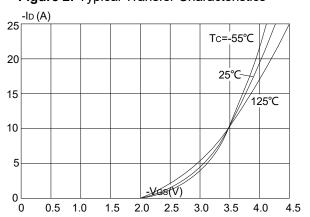


Figure 4: Body Diode Characteristics

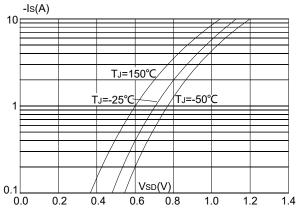


Figure 6: Capacitance Characteristics

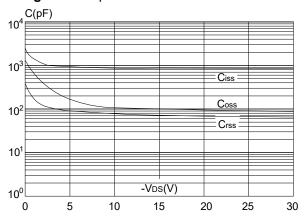




Figure 7: Normalized Breakdown Voltage vs. Junction Temperature

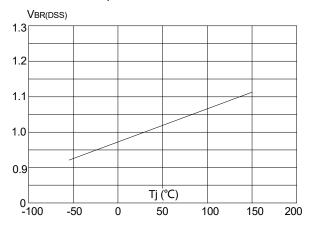


Figure 9: Maximum Safe Operating Area

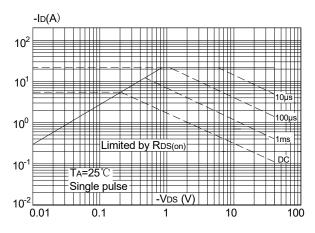


Figure.11: Maximum Effective Transient Thermal Impedance, Junction-to-Ambient

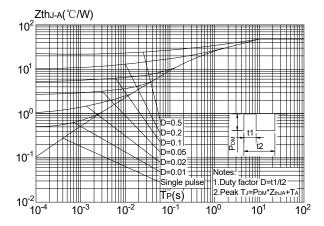


Figure 8: Normalized on Resistance vs. Junction Temperature

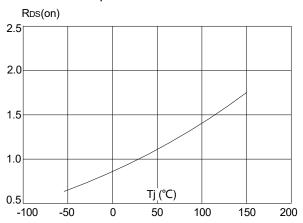
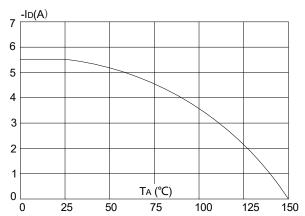
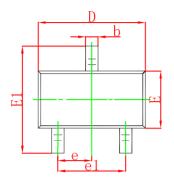


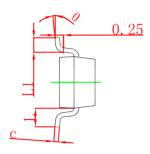
Figure 10: Maximum Continuous Drain Current vs. Ambient Temperature

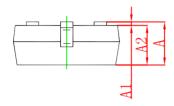




SOT-23 Package Outline Dimensions

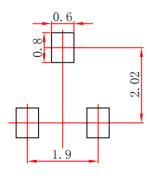






Symbol	Dimensions In Millimeters		Dimensions In Inches		
Зупроі	Min	Max	Min	Max	
Α	0.900	1.150	0.035	0.045	
A1	0.000	0.100	0.000	0.004	
A2	0.900	1.050	0.035	0.041	
b	0.300	0.500	0.012	0.020	
С	0.080	0.150	0.003	0.006	
D	2.800	3.000	0.110	0.118	
Е	1.200	1.400	0.047	0.055	
E1	2.250	2.550	0.089	0.100	
е	0.950 TYP		0.037 TYP		
e1	1.800	2.000	0.071	0.079	
L	0.550	REF	0.022	0.022 REF	
L1	0.300	0.500	0.012	0.020	
θ	0°	8°	0°	8°	

SOT-23 Suggested Pad Layout



Note:

- 1.Controlling dimension:in millimeters.
- 2.General tolerance:± 0.05mm.
 3.The pad layout is for reference purposes only.

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